

DOCKET NO: 240800US-2S DIV

IN THE UNITED STATES PATENT & TRADEMARK OFFICE

IN RE APPLICATION OF :
NORIHISA ARAI : ATTN: APPLICATION DIVISION
SERIAL NO: NEW U.S. APPLICATION :
FILED: HEREWITH :
FOR: METHOD OF MANUFACTURING :
SEMICONDUCTOR DEVICE
INCLUDING PROCESS FOR
IMPLANTING IMPURITIES INTO
SUBSTRATE VIA MOS
TRANSISTOR GATE ELECTRODE
AND GATE INSULATION FILM

PRELIMINARY AMENDMENT

COMMISSIONER FOR PATENTS
ALEXANDRIA, VIRGINIA 22313

SIR:

Prior to an action on the merits, please amend this application as follows:

Amendments to the Specification begin on page 2 of this paper.

Amendments to the Claims are reflected in the listing of claims which begins on
page 3 of this paper.

Remarks/Arguments begin on page 4 of this paper.